

# 2SC2315 2SC2316

## Silicon NPN Triple Diffused Mesa ☆Super Beta Transistor

**Application Example:**  
General Purpose

●Outline Drawing 1 .....MT-25(TO220)

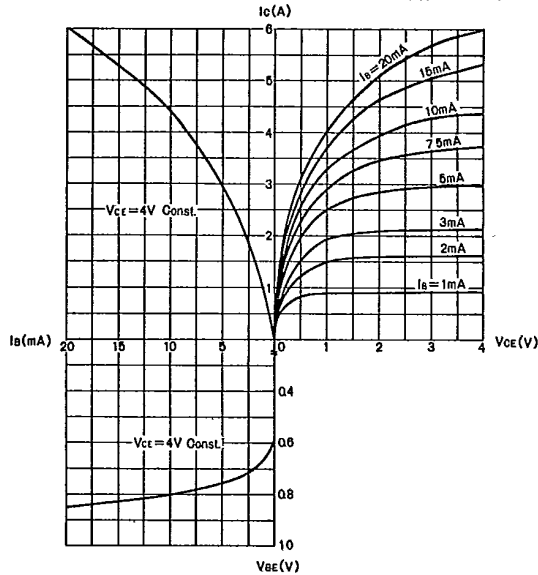
### Absolute Maximum Ratings

Symbol	2SC2315	2SC2316	Unit
$V_{CB0}$	80	100	V
$V_{CE0}$	60	80	V
$V_{EBO}$	6		V
$I_C$	6		A
$I_B$	3		A
$P_C$	50 ( $T_{FL}=25^{\circ}C$ )		W
$T_J$	150		$^{\circ}C$
$T_{stg}$	-55~+150		$^{\circ}C$

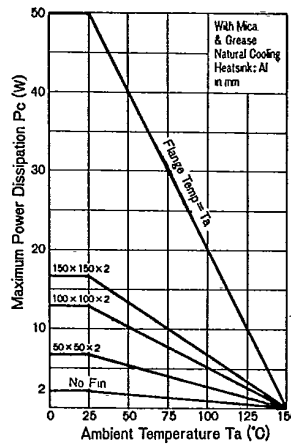
### Electrical Characteristics

Symbol	Conditions	2SC2315	2SC2316	Unit
$I_{CBO}$		100max	100max	$\mu A$
	$V_{CB}=$	80	100	V
$I_{EBO}$	$V_{EB}=6V$	1.0max		mA
$V_{(BR)CEO}$	$I_C=25mA$	60min	80min	V
$h_{FE}$	$V_{CE}=4V, I_C=0.5A$	500min		
$V_{CE(sat)}$	$I_C=3A, I_B=0.06A$	1.0max		V
$f_T$	$V_{CE}=12V, I_E=-0.5A$	30typ		MHz

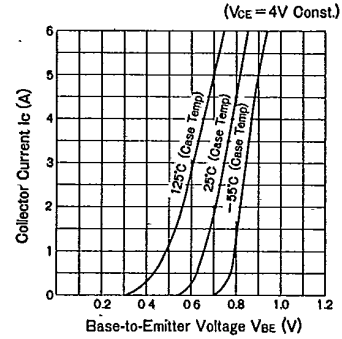
### Common Emitter Characteristics (Typical Value)



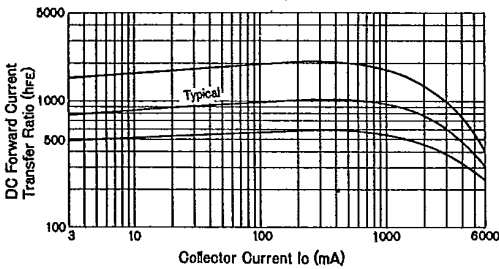
### Power Derating



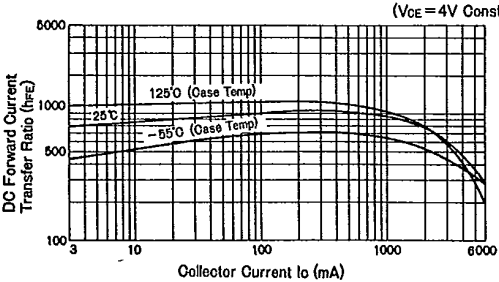
### Temperature Characteristics



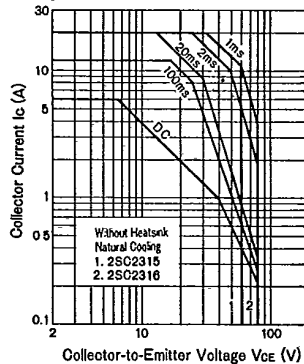
### DC Current Gain Characteristics



### DC Current Gain Temperature Characteristics



### Maximum Areas For Safe Operation (ASO) (Single Pulse)



### Collector-to-Emitter Saturation Characteristics

